

Forming Resistive Random Access Memories Together With Fuse Arrays

Abstract of the Disclosure

5 A resistive random access memory array may be formed on the same
substrate with a fuse array. The random access memory and the fuse array may
use the same active material. For example, both the fuse array and the memory
array may use a chalcogenide material as the active switching material. The main
array may use a pattern of perpendicular sets of trench isolations and the fuse array
may only use one set of parallel trench isolations. As a result, the fuse array may
10 have a conductive line extending continuously between adjacent trench isolations.
In some embodiments, this continuous line may reduce the resistance of the
conductive path through the fuses.

FIG. 1